

AMENDMENT TO THE CLAIMS

Please **CANCEL** claims 1-13 and 27-30.

A copy of all pending claims and a status of the claims is provided below.

Claims 1-13. (cancel)

Claim 14. (original) A semiconductor structure comprising:

a semiconductor substrate;

a first active device formed on the substrate, the first active device having a first dielectric gate, which has a first concentration of nitrogen; and

a second active device formed on the substrate, the second active device having a second dielectric gate, which has a second concentration of nitrogen different than the first concentration of nitrogen.

Claim 15. (original) A semiconductor structure according to claim 14, wherein:

the first dielectric gate has a first thickness susceptible to appreciable dopant diffusion and current leakage; and

the second dielectric gate has a second thickness susceptible to appreciable dopant diffusion and current leakage.

Claim 16. (original) A semiconductor structure according to claim 15, wherein the second concentration of nitrogen is less than the first concentration of nitrogen.

Claim 17. (original) A semiconductor structure according to claim 16, wherein the second active device is a p-channel field effect transistor and the first active device is an n-channel field effect transistor.

Claim 18. (original) A semiconductor structure according to claim 14, wherein the first dielectric gate has a first thickness being susceptible to appreciable dopant diffusion or current leakage; and the second dielectric gate having a second thickness not being susceptible to appreciable dopant diffusion or current leakage.

Claim 19. (original) A semiconductor structure according to claim 18, wherein the second concentration of nitrogen is less than the first concentration of nitrogen.

Claim 20. (original) A semiconductor structure according to claim 15, wherein the first thickness and second thickness are less than about fifty angstroms.

Claim 21. (original) A semiconductor structure according to claim 18, wherein the first thickness is less than about fifty angstroms; and the second thickness is about fifty angstroms or greater.

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Claim 22. (original) A semiconductor structure according to claim 14, wherein the first concentration of nitrogen and the second concentration of nitrogen were selectively introduced by one or more processes including one of:

- rapid thermal nitridation;
- furnace nitridation;
- remote plasma nitridation;
- decoupled plasma nitridation;
- well implantation; and
- polysilicon implantation.

Claim 23. (original) A semiconductor structure according to claim 14, wherein the first concentration of nitrogen is about 8×10^{14} to 1×10^{22} atoms/centimeter².

Claim 24. (original) A semiconductor structure according to claim 14, wherein the first concentration of nitrogen is sufficient to prevent appreciable gate leakage and dopant penetration in the first dielectric gate without causing an appreciable threshold-voltage shift in the first dielectric gate.

Claim 25. (original) A semiconductor structure according to claim 24, wherein the second concentration of nitrogen is about 1×10^{13} to 1×10^{15} atoms/centimeter².

Claim 26. (original) A semiconductor structure according to claim 14, wherein the second concentration of nitrogen is sufficient to prevent appreciable gate leakage and dopant penetration in the second dielectric gate without causing an appreciable threshold-voltage shift in the second dielectric gate.

Claims 27-30. (cancel)